

[查询M54522FP供应商](#)

[捷多邦，专业PCB打样工厂，24小时加急出货](#)

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M54522P/FP

8-UNIT 400mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE

DESCRIPTION

M54522P and M54522FP are eight-circuit Darlington transistor arrays with clamping diodes. The circuits are made of NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

- High breakdown voltage ($BV_{CEO} \geq 40V$)
- High-current driving ($I_C(max) = 400mA$)
- With clamping diodes
- Driving available with PMOS IC output
- Wide operating temperature range ($T_a = -20$ to $+75^{\circ}C$)

APPLICATION

Drives of relays and printers, digit drives of indication elements (LEDs and lamps), and interfaces between microcomputer output and high-current or high-voltage systems

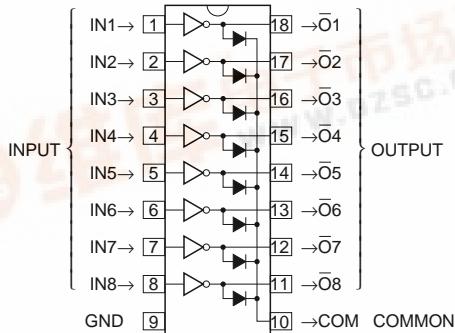
FUNCTION

The M54522P and M54522FP each have eight circuits consisting of NPN Darlington transistors. These ICs have resistance of $20k\Omega$ between input transistor bases and input pins. A spike-killer clamping diode is provided between each output pin (collector) and COM pin. The output transistor emitters are all connected to the GND pin (pin 8).

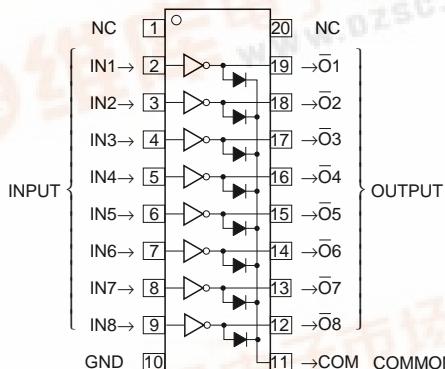
The collector current is 400mA maximum. Collector-emitter supply voltage is 40V maximum.

The M54522FP is enclosed in a molded small flat package, enabling space-saving design.

PIN CONFIGURATION



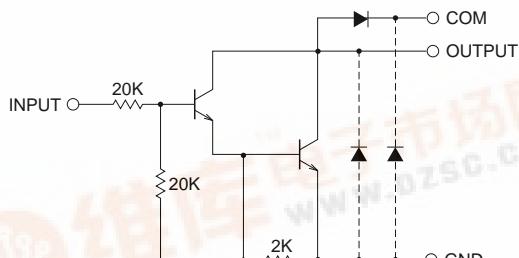
Package type 18P4G(P)



Package type 20P2N-A(FP)

NC : No connection

CIRCUIT DIAGRAM



The eight circuits share the COM and GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : Ω

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M54522P/FP

8-UNIT 400mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE

ABSOLUTE MAXIMUM RATINGS (Unless otherwise noted, $T_a = -20 \sim +75^\circ\text{C}$)

Symbol	Parameter	Conditions	Ratings	Unit
VCEO	Collector-emitter voltage	Output, H	-0.5 ~ +40	V
IC	Collector current	Current per circuit output, L	400	mA
VI	Input voltage		-0.5 ~ +40	V
IF	Clamping diode forward current		400	mA
VR	Clamping diode reverse voltage		40	V
Pd	Power dissipation	$T_a = 25^\circ\text{C}$, when mounted on board	1.79(P)/1.10(FP)	W
Topr	Operating temperature		-20 ~ +75	$^\circ\text{C}$
Tstg	Storage temperature		-55 ~ +125	$^\circ\text{C}$

RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, $T_a = -20 \sim +75^\circ\text{C}$)

Symbol	Parameter	Limits			Unit
		min	typ	max	
VO	Output voltage	0	—	40	V
IC	Collector current (Current per 1 circuit when 8 circuits are coming on simultaneously)	Duty Cycle P : no more than 7% FP : no more than 5%	0	—	400 mA
		Duty Cycle P : no more than 30% FP : no more than 20%	0	—	200
VIH	"H" input voltage	IC \leq 400mA	8	—	V
		IC \leq 200mA	4	—	
VIL	"L" input voltage	0	—	0.5	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, $T_a = -20 \sim +75^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
V (BR) CEO	Collector-emitter breakdown voltage	ICEO = 100 μA	40	—	—	V
VCE (sat)	Collector-emitter saturation voltage	VI = 8V, IC = 400mA	—	1.15	2.4	V
		VI = 4V, IC = 200mA	—	0.95	1.6	
Ii	Input current	VI = 17V	0.3	0.85	1.8	mA
VF	Clamping diode forward voltage	IF = 400mA	—	1.5	2.4	V
IR	Clamping diode reverse current	VR = 40V	—	—	100	μA
hFE	DC amplification factor	VCE = 4V, IC = 300mA, $T_a = 25^\circ\text{C}$	1000	8000	—	—

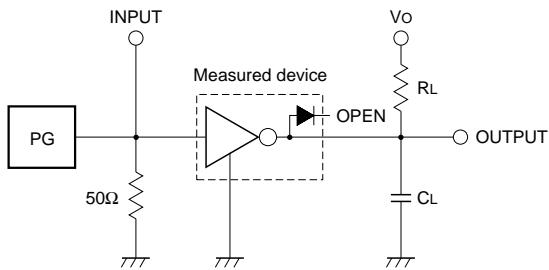
* : The typical values are those measured under ambient temperature (T_a) of 25°C . There is no guarantee that these values are obtained under any conditions.

SWITCHING CHARACTERISTICS (Unless otherwise noted, $T_a = 25^\circ\text{C}$)

Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
ton	Turn-on time	CL = 15pF (note 1)	—	30	—	ns
toff	Turn-off time		—	930	—	ns

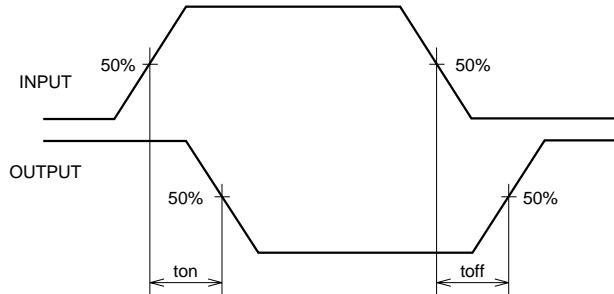
8-UNIT 400mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE

NOTE 1 TEST CIRCUIT

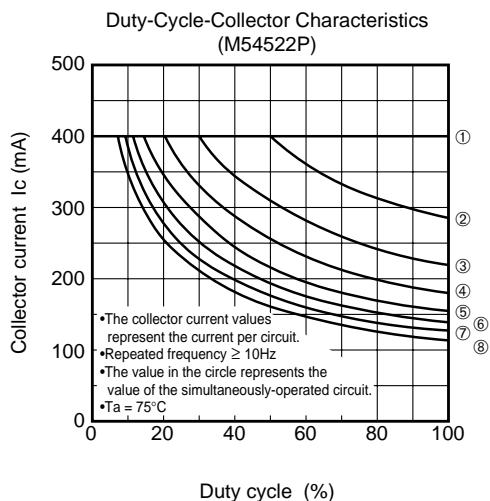
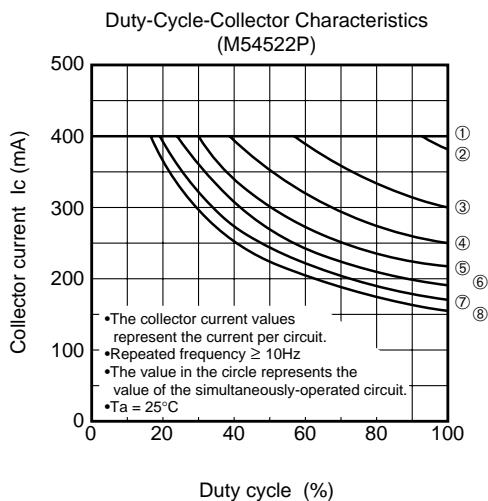
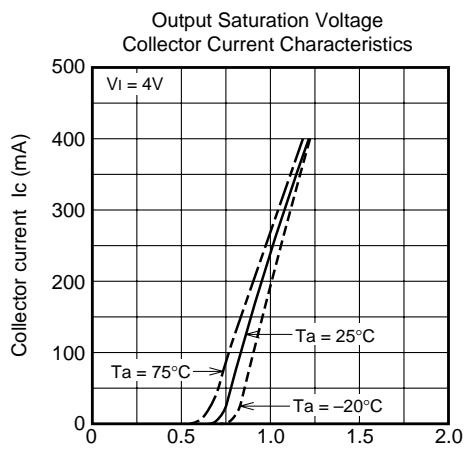
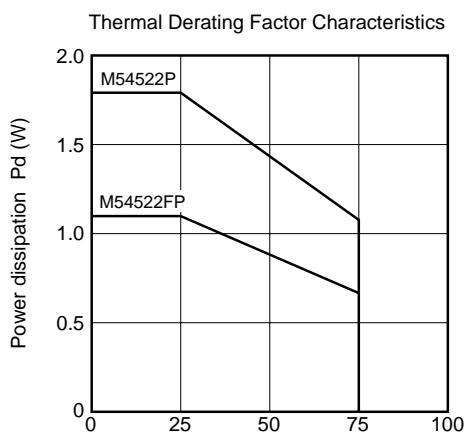


- (1) Pulse generator (PG) characteristics : PRR = 1kHz,
 $t_w = 10\mu s$, $t_r = 6ns$, $Z_0 = 50\Omega$
 $V_{IN} = 0$ to $8V$
(2) Input-output conditions : $RL = 25\Omega$, $VO = 10V$
(3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM



TYPICAL CHARACTERISTICS



MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M54522P/FP

8-UNIT 400mA DARLINGTON TRANSISTOR ARRAY WITH CLAMP DIODE

